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| First Named Inventor  | Leonard Forbes    |
| Serial No.  | 10/785,310        |
| Filing Date   | February 24, 2004 |
| Group Art Unit  | 2818              |
| Examiner Name   | Unknown           |
| Confirmation No.  | 9673              |
| Attorney Docket No.   | 400.264US01       |
| Title: 4F2 EEPROM NROM MEMORY ARRAYS<br>WITH VERTICAL DEVICES |                   |

**INFORMATION DISCLOSURE  
STATEMENT  
FORM PTO-1449**

Sheet 1 of 7

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| Examiner Signature | Tu-Sue HO | Date Considered | Apr. 2005 |
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| Title: 4F2 EEPROM NROM MEMORY ARRAYS<br>WITH VERTICAL DEVICES |                   | Sheet 3 of 7 |  |

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| Examiner Signature   | <i>Tu-Tu Ho</i> | Date Considered | <i>Apr. 2005</i> |
| *Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |                 |                 |                  |

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|---|-------------------|---|
| First Named Inventor  | Leonard Forbes    | <b>INFORMATION DISCLOSURE<br/>STATEMENT<br/>FORM PTO-1449</b> |
| Serial No.  | 10/785,310        |   |
| Filing Date   | February 24, 2004 |   |
| Group Art Unit  | 2818              |   |
| Examiner Name   | Unknown           |   |
| Confirmation No.  | 9673              |   |
| Attorney Docket No.   | 400.264US01       |   |
| Title: 4F2 EEPROM NROM MEMORY ARRAYS<br>WITH VERTICAL DEVICES |                   | Sheet 7 of 7  |

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| *Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant. |                 |                 |                  |

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|  |                   |  |
|--|-------------------|--|
| First Named Inventor                                       | Leonard Forbes    | <b>SUPPLEMENTAL<br/>INFORMATION DISCLOSURE<br/>STATEMENT<br/>FORM PTO-1449</b> |
| Serial No.   | 10/785,310        |  |
| Filing Date  | February 24, 2004 |  |
| Group Art Unit   | 2818              |  |
| Examiner Name  | Unknown           |  |
| Confirmation No.   | 9673              |  |
| Attorney Docket No.  | 400.264US01       |  |
| Title: 4F2 EEPROM NROM MEMORY ARRAYS WITH VERTICAL DEVICES |                   |  |

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| Examiner Initials                | Foreign Patent |     | Name | Publication Date | Translation |
|                                  | Country        | No. |      |                  |             |
|                                  |                |     |      |                  |             |
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| Examiner Initials       | Author, Title, Date, Pages, etc. |
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| Examiner Signature | TU-TU HO | Date Considered | Apr 2005 |
|--------------------|----------|-----------------|----------|

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